				F	REVISI	ONS										
L查询"5962-8944101VCA"供应商 ^{ESCRIPTION}								DA	ATE (YI	R-MO-I	DA)		APPF	ROVED		
A	Changes in accord									92-0)1-24			M. A	. FRYE	
В	Drawing updated to	o reflect current	t requiremen	ts ro)				01-06-19			R. MONNIN				
С	Add device class V	device ro								02-0)3-29			R. M	ONNIN	
THE ORIGINAL	FIRST SHEET OF T	HIS DRAWING	HAS BEEN	REPLA	ACED.											
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REV STATUS		REV	С	С	С	С	С	С	С	С	С	С	С			
OF SHEETS		SHEET	1	2	3	4	5	6	7	8	9	10	11			
PMIC N/A PREPARED BY JOSEPH A. KERBY STANDARD MICROCIRCUIT CHECKED BY CHARLES E. BESORE				DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216 http://www.dscc.dla.mil												
DRAWING THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS AND AGENCIES OF THE DEPARTMENT OF DEFENSE		APPROVED BY MONICA L. POELKING DRAWING APPROVAL DATE 90-03-15				MICROCIRCUIT, LINEAR, ISOLATED FEEDBACK GENERATOR, MONOLITHIC SILICON				СК						
AMS	SC N/A	REVISION L	EVEL C			ļ	ZE A		GE CC 67268			ł	5962·	-8944	1	
						SHEI			1	OF	11					

DSCC FORM 2233 APR 97

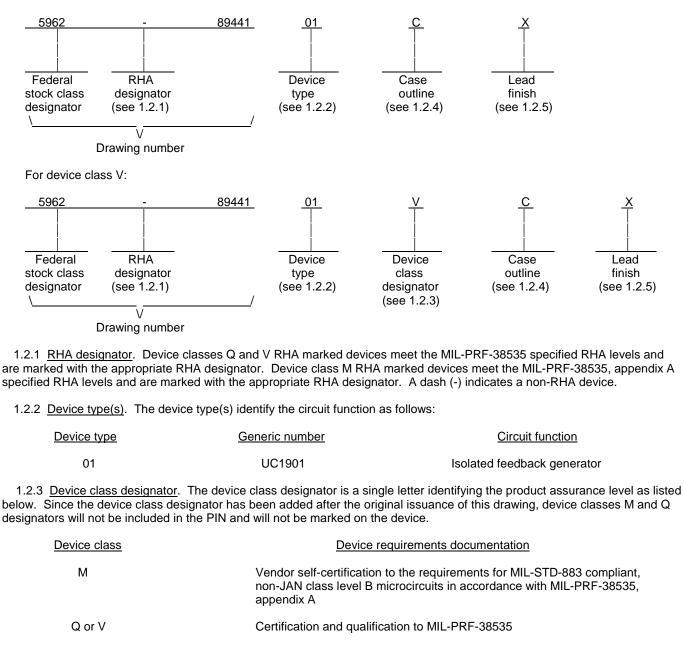
DISTRIBUTION STATEMENT A. Approved for public release; distribution is unlimited.

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1.1 <u>Scope</u>. This drawing documents two product assurance class levels consisting of high reliability (device classes Q and M) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels are reflected in the PIN.

1.2 PIN. The PIN is as shown in the following examples.

For device classes M and Q:



	-		
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Outline letter	Descriptive designator	<u>Terminals</u>	Package	style
C 2	GDIP1-T14 or CDIP2-T14 CQCC1-N20	14 20	Dual-in-line Square leadles	s chip carrier
2.5 <u>Lead finish</u> . The le endix A for device class	ead finish is as specified in MIL-PR s M.	F-38535 for device	e classes Q and V or MIL $$	PRF-38535,
3 Absolute maximum	ratings. <u>1/ 2</u> /			
Input supply voltage (\	/ _{IN})	+40 V dc		
-	ent			
	e			
	nt			
	、 、	0.5 V dc to +	35 V dc	
Power dissipation (PD	,			
-				
	(TJ)			
	ange		0°C	
	dering, 10 seconds) Inction-to-case (θ _{JC})		1925	
-		See MIL-STD	-1000	
	nction-to-ambient (θ _{JA}):	80°C/W		
1 Government specific of this drawing to the	MENTS cation, standards, and handbooks. extent specified herein. Unless oth nt of Defense Index of Specification	erwise specified, th	ne issues of these docum	ents are those liste
1 <u>Government specific</u> of this drawing to the e issue of the Departmer citation.	cation, standards, and handbooks. extent specified herein. Unless oth	erwise specified, th	ne issues of these docum	ents are those liste
1 <u>Government specific</u> of this drawing to the e issue of the Departmer citation. PECIFICATION	cation, standards, and handbooks. extent specified herein. Unless oth nt of Defense Index of Specification	erwise specified, th	ne issues of these docum	ents are those liste
of this drawing to the e	cation, standards, and handbooks. extent specified herein. Unless oth nt of Defense Index of Specification	erwise specified, th	ne issues of these docum	ents are those liste
1 <u>Government specific</u> of this drawing to the e issue of the Departmer citation. PECIFICATION DEPARTMENT OF DE	cation, standards, and handbooks. extent specified herein. Unless oth nt of Defense Index of Specification	erwise specified, th s and Standards (I	ne issues of these docum DoDISS) and supplement	ents are those liste
1 <u>Government specific</u> of this drawing to the e issue of the Departmen citation. PECIFICATION DEPARTMENT OF DE MIL-PRF-38535 - 1 Stresses above the ab maximum levels may of All voltages referenced	Exation, standards, and handbooks. Extent specified herein. Unless oth at of Defense Index of Specification EFENSE Integrated Circuits, Manufacturing, esolute maximum rating may cause degrade performance and affect rel d to ground. Currents are positive above $T_A = +50^{\circ}C$ for case C. Def	erwise specified, th s and Standards (I General Specificat permanent damag iability. into, and negative o	ne issues of these docum DoDISS) and supplement ion for. le to the device. Extende put of the specified termin	ents are those liste thereto, cited in the d operation at the nals.
1 <u>Government specific</u> of this drawing to the e issue of the Departmen citation. PECIFICATION DEPARTMENT OF DE MIL-PRF-38535 - I Stresses above the ab maximum levels may of All voltages referenced Derate at +10 mW/°C Derate at +16 mW/°C	Exation, standards, and handbooks. Extent specified herein. Unless oth at of Defense Index of Specification EFENSE Integrated Circuits, Manufacturing, esolute maximum rating may cause degrade performance and affect rel d to ground. Currents are positive above $T_A = +50^{\circ}C$ for case C. Def	erwise specified, th s and Standards (I General Specificat permanent damag iability. into, and negative o rate at +9 mW/°C a	ne issues of these docum DoDISS) and supplement ion for. le to the device. Extende put of the specified termin	ents are those liste thereto, cited in the d operation at the nals. e 2.
1 <u>Government specific</u> of this drawing to the e issue of the Departmen citation. PECIFICATION DEPARTMENT OF DE MIL-PRF-38535 - 1 Stresses above the ab maximum levels may of All voltages referenced Derate at +10 mW/°C Derate at +16 mW/°C STA	Exation, standards, and handbooks. extent specified herein. Unless oth at of Defense Index of Specification EFENSE Integrated Circuits, Manufacturing, psolute maximum rating may cause degrade performance and affect rel d to ground. Currents are positive above $T_A = +50^{\circ}C$ for case C. Def above $T_C = +25^{\circ}C$.	erwise specified, th s and Standards (I General Specificat permanent damag iability. into, and negative o rate at +9 mW/°C a	ne issues of these docum DoDISS) and supplement ion for. le to the device. Extende put of the specified termin	ents are those liste thereto, cited in the d operation at the nals.

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DEPARTMENT OF DEFENSE

MIL-STD-883	-	Test Method Standard Microcircuits.
MIL-STD-1835	-	Interface Standard Electronic Component Case Outlines.

HANDBOOKS

DEPARTMENT OF DEFENSE

MIL-HDBK-103 - List of Standard Microcircuit Drawings. MIL-HDBK-780 - Standard Microcircuit Drawings.

(Unless otherwise indicated, copies of the specification, standards, and handbooks are available from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 <u>Item requirements</u>. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. The individual item requirements for device class M shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein.

3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V or MIL-PRF-38535, appendix A and herein for device class M.

3.2.1 Case outlines. The case outlines shall be in accordance with 1.2.4 herein.

3.2.2 <u>Terminal connections</u>. The terminal connections shall be as specified on figure 1.

3.2.4 Block diagram. The block diagram shall be as specified on figure 2.

3.3 <u>Electrical performance characteristics and post irradiation parameter limits</u>. Unless otherwise specified herein, the electrical performance characteristics and post irradiation parameter limits are as specified in table I and shall apply over the full ambient operating temperature range.

3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are defined in table I.

3.5 <u>Marking</u>. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked as listed in MIL-HDBK-103. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535. Marking for device class M shall be in accordance with MIL-PRF-38535, appendix A.

3.5.1 <u>Certification/compliance mark</u>. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535. The compliance mark for device class M shall be a "C" as required in MIL-PRF-38535, appendix A.

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查询"5962-8944101VC	4"供应商	ABLE I. Electrical perf	formance	characteris	<u>stics</u> .			
Test	Symbol	Conditions $1/2$ -55°C \leq T _A \leq +12 unless otherwise spe	5°C Group A			Limits		Unit
Ourach						Min	Max	
Supply								
Supply current	ICC	V _{IN} = +35 V		1,2,3	01		8	mA
Reference section	I	L	I					I
Output voltage	VREF			1	01	1.485	1.515	V
			-	2,3		1.470	1.530	-
Line regulation	V _{RLN}	V _{IN} = +4.5 V to +35	V	1,2,3	01		10	mV
Load regulation	V _{RLD}	$I_{OUT} = 0 \text{ mA to } -5 \text{ m}$		1,2,3	01		10	mV
Short circuit current	los	T _J = +25°C		1	01		-55	mA
Error amplifier section (to con								
Input offset voltage	VIO	V _{CM} = +1.5 V		1,2,3	01		4	mV
Input bias current	I _{IB}	V _{CM} = +1.5 V		1,2,3	01		-3	μA
Input offset current	IIO	V _{CM} = +1.5 V		1,2,3	01		1	μA
Small signal open loop gain	A _{OL}			4,5,6	01	40		dB
Common mode rejection ratio	CMRR	V _{CM} = +0.5 V to 7.5	V	4,5,6	01	60		dB
Power supply rejection ratio	PSRR	V_{IN} = +5 V to +25 V		4,5,6	01	80		dB
Output voltage swing	ΔVO			1,2,3	01	0.4		V
Maximum sink current	I _{SINK}			1,2,3	01	90		μA
Maximum source current	I _{SRC}			1,2,3	01	-2		mA
Modulator / drivers section (fr	om comper	sation terminal)						I
Voltage gain	A _V			4,5,6	01	11	13	dB
Output swing	Vo			1,2,3	01	±1.6		V
Driver sink current	I _{SINK}			1,2,3	01	500		μA
Driver source current	I _{SRC}			1,2,3	01	-15		mA
See footnotes at end of table.								
MICROCIRCU			SIZ A				596	2-89441
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		. Electrical performance chara					
Test	Symbol	$\begin{array}{l} Conditions \ \underline{1}/\underline{2}/\\ -55^\circ C \leq T_A \leq +125^\circ C\\ \text{unless otherwise specified} \end{array}$	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Oscillator section							
Initial accuracy	ACC		4	01	140	160	kHz
			5,6		130	170	_
Line sensitivity	V _{LINE}	V _{IN} = +5 V dc to +35 V dc	4,5,6	01		0.35	%/V
External clock low threshold	V _{THL}	C _T pin = V _{IN}	1,2,3	01	0.5		V
External clock high threshold	VTHH	C _T pin = V _{IN}	1,2,3	01		1.6	V
Status indicator section	•		1				
Input voltage window	VIN	At error amplifier inputs,	1,2,3	01	±135	±165	mW
		V _{CM} = +1.5 V dc					
Saturation voltage	VSAT	Error amplifier input =	1,2,3	01		0.45	V
	_	$V_{INV} - V_{NI} = 0 V,$					
		I _{SINK} = 1.6 mA					
Maximum output current	lo	Error amplifier input =	1,2,3	01	8		mA
	-	$V_{INV} - V_{NI} = 0 V,$					
		STATUS OUTPUT pin = 3 V dc					
Leakage current	١L	STATUS OUTPUT pin = +40 V dc, error amplifier	1,2,3	01		1	μA
		$V_{INV} - V_{NI} = \pm 0.2 V$					

<u>1</u>/ Unless otherwise specified, V_{IN} = +10 V dc, R_T = 10 k Ω , and C_T = 820 pF.

2/ The error amplifier compensation terminal is intended as a source of feedback to the amplifier's inverting input terminal. For most applications, a series DC blocking capacitor should be part of the feedback network. The amplifier is internally compensated for unity feedback.

The waveform at the driver outputs is a squarewave with an amplitude that is proportional to the error amplifier input signal. There is a fixed 12 dB of gain from the error amplifier compensation pin to the modulator driver outputs. The frequency of the output waveform is controlled by either the internal oscillator or an external clock signal. With the internal oscillator, the squarewave will have a fixed 50 percent duty cycle. If the internal oscillator is disabled by connecting C_T pin to V_{IN} , then the frequency and the duty cycle of the output will be determined by the input clock waveform at the external clock pin. If the oscillator remains disabled and there is no clock at the external clock pin, there will be a linear 12 dB of signal gain to one or the other of the driver outputs depending on the dc state of the external clock pin.

The driver outputs are emitter followers which will source a minimum of 15 mA of current. The sink current, internally limited at 700 μ A, can be increased by adding resistors to ground at the driver outputs.

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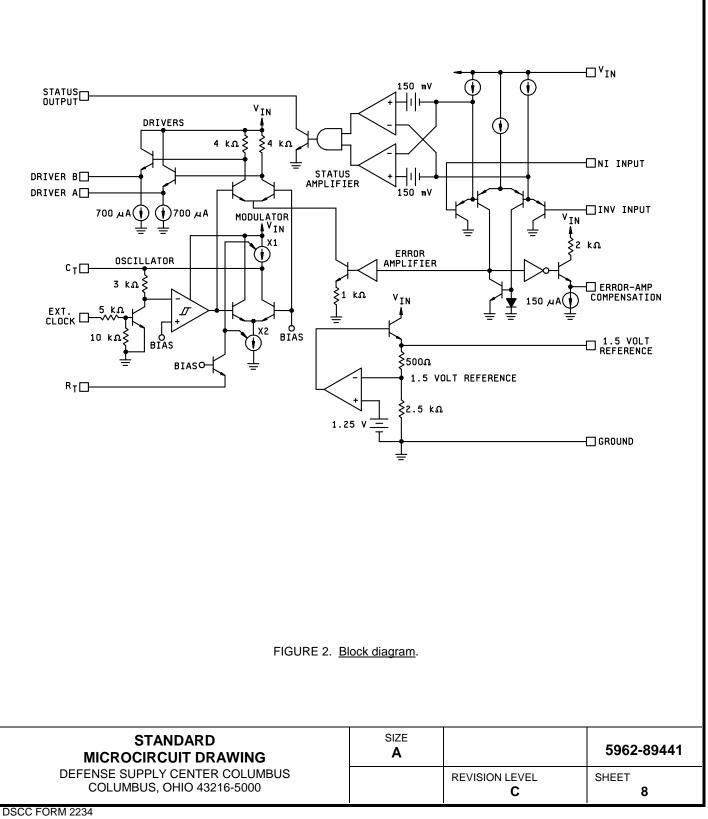
Device type	01				
Case outlines	С	2			
Terminal number	Terminal symbol				
1	CT	NC			
2	EXTERNAL CLOCK	CT			
3	NC	NC			
4	DRIVER B	EXTERNAL CLOCK			
5	DRIVER A	DRIVER B			
6	NC	NC			
7	GROUND	DRIVER A			
8	R _T	NC			
9	V _{REF}	NC			
10	NON-INVERTING INPUT	GROUND			
11	INVERTING INPUT	NC			
12	COMPENSATION	R _T			
13	STATUS OUTPUT	V _{REF}			
14	+V _{IN}	NC			
15		NON-INVERTING INPUT			
16		NC			
17		INVERTING INPUT			
18		COMPENSATION			
19		STATUS OUTPUT			
20		+V _{IN}			

NC = No connection

FIGURE 1. Terminal connections.

STANDARD	SIZE		
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3.6. Certificate of compliance in For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6.2 herein). The certificate of compliance submitted to DSCC-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein or for device class M, the requirements of MIL-PRF-38535, appendix A and herein.

3.7 <u>Certificate of conformance</u>. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 or for device class M in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.

3.8 <u>Notification of change for device class M</u>. For device class M, notification to DSCC-VA of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change as defined in MIL-PRF-38535, appendix A.

3.9 <u>Verification and review for device class M</u>. For device class M, DSCC, DSCC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

3.10 <u>Microcircuit group assignment for device class M</u>. Device class M devices covered by this drawing shall be in microcircuit group number 110 (see MIL-PRF-38535, appendix A).

4. QUALITY ASSURANCE PROVISIONS

4.1 <u>Sampling and inspection</u>. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. For device class M, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.

4.2 <u>Screening</u>. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection.

- 4.2.1 Additional criteria for device class M.
 - a. Burn-in test, method 1015 of MIL-STD-883.
 - (1) Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
 - (2) $T_A = +125^{\circ}C$, minimum.
 - b. Interim and final electrical test parameters shall be as specified in table II herein.
- 4.2.2 Additional criteria for device classes Q and V.
 - a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.
 - b. Interim and final electrical test parameters shall be as specified in table II herein.
 - c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.

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TABLE II. Electrical test requirements.

Test requirements	Subgroups (in accordance with MIL-STD-883, method 5005, table I)	Subgroups (in accordance with MIL-PRF-38535, table III)		
	Device class M	Device class Q	Device class V	
Interim electrical parameters (see 4.2)	1	1	1	
Final electrical parameters (see 4.2)	1,2,3,4,5,6 <u>1</u> /	1,2,3, <u>1</u> / 4,5,6	1,2,3, <u>1</u> / 4,5,6	
Group A test requirements (see 4.4)	1,2,3,4,5,6	1,2,3,4,5,6	1,2,3,4,5,6	
Group C end-point electrical parameters (see 4.4)	1	1	1	
Group D end-point electrical parameters (see 4.4)	1	1	1	
Group E end-point electrical parameters (see 4.4)				

1/ PDA applies to subgroup 1.

4.3 <u>Qualification inspection for device classes Q and V</u>. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4 <u>Conformance inspection</u>. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections and as specified herein. Quality conformance inspection for device class M shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4.1 Group A inspection.

- a. Tests shall be as specified in table II herein.
- b. Subgroups 7, 8, 9, 10, and 11 in table I, method 5005 of MIL-STD-883 shall be omitted.

4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table II herein.

4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:

- a. Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.
- b. $T_A = +125^{\circ}C$, minimum.
- c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

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4.4.2.2. Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved diternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.

4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table II herein.

4.4.4 <u>Group E inspection</u>. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).

- a. End-point electrical parameters shall be as specified in table II herein.
- b. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535, appendix A for the RHA level being tested. All device classes must meet the post irradiation end-point electrical parameter limits as defined in table I at $T_{A} = +25^{\circ}C$ after exposure, to the subgroups specified in table II herein.

c. When specified in the purchase order or contract, a copy of the RHA delta limits shall be supplied.

5. PACKAGING

5.1 <u>Packaging requirements</u>. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

6. NOTES

6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.

6.1.1 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.

6.2 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished using DD Form 1692, Engineering Change Proposal.

6.3 <u>Record of users</u>. Military and industrial users should inform Defense Supply Center Columbus when a system application requires configuration control and which SMD's are applicable to that system. DSCC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DSCC-VA, telephone (614) 692-0544.

6.4 <u>Comments</u>. Comments on this drawing should be directed to DSCC-VA, Columbus, Ohio 43216-5000, or telephone (614) 692-0547.

6.5 <u>Abbreviations, symbols, and definitions</u>. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.

6.6 Sources of supply.

6.6.1 <u>Sources of supply for device classes Q and V</u>. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DSCC-VA and have agreed to this drawing.

6.6.2 <u>Approved sources of supply for device class M</u>. Approved sources of supply for class M are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DSCC-VA.

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STANDARD MICROCIRCUIT DRAWING BULLETIN

查询"5962-8944101VCA"供应商

DATE: 02-03-29

Approved sources of supply for SMD 5962-89441 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DSCC-VA. This bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535.

Standard microcircuit drawing PIN <u>1</u> /	Vendor CAGE number	Vendor similar PIN <u>2</u> /
5962-8944101CA	01295	UC1901J/883B
5962-89441012A	01295	UC1901L/883B
5962-8944101VCA	01295	UC1901JQMLV

- 1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.
- <u>2</u>/ <u>Caution</u>. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

Vendor CAGE <u>number</u> Vendor name and address

01295

Texas Instruments, Incorporated Semiconductor Group 8505 Forest Lane P.O. Box 660199 Dallas, TX 75243 Point of contact: U.S. Highway 75 South P.O. Box 84, M/S 853 Sherman, TX 75090-9493

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